

P-CHANNEL ENHANCEMENT MODE FIELD EFFECT TRANSISTOR

Product Summary

$V_{(BR)DSS}$	$R_{DS(ON)}$	Package	I_D $T_A = +25^\circ C$
-50V	10Ω $V_{GS} = -5V$	SOT323	-130mA

Features

- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- **Totally Lead-Free & Fully RoHS compliant (Note 1)**
- **Halogen and Antimony Free. "Green" Device (Note 2)**

Description

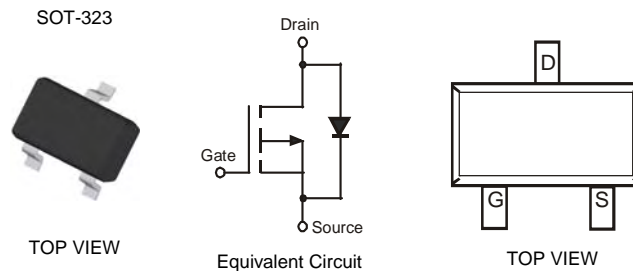
This MOSFET has been designed to minimize the on-state resistance ($R_{DS(on)}$) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

- General Purpose Interfacing Switch
- Power Management Functions
- Analog Switch

Mechanical Data

- Case: SOT323
- Case Material: Molded Plastic, "Green" Molding Compound, UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020C
- Terminal Connections: See Diagram
- Terminals: Solderable per MIL-STD-202, Method 208
- Lead Free Plating (Matte Tin Finish annealed over Alloy 42 leadframe). **e3**
- Weight: 0.006 grams (approximate)

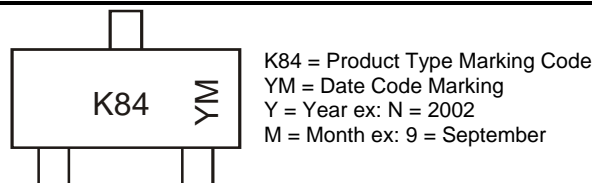


Ordering Information (Notes 3)

Part Number	Case	Packaging
BSS84W-7-F	SOT323	3000/Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
 2. Halogen and Antimony free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 3. For packaging details, go to our website at <http://www.diodes.com/datasheets/ap02007.pdf>.

Marking Information



Date Code Key

Year	1998	1999	2000	2001	2002	2003	2004	2005	2006	2007	2008	2009	2010	2011	2012
Code	J	K	L	M	N	P	R	S	T	U	V	W	X	Y	Z

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Maximum Ratings (@T_A = 25°C unless otherwise specified)

Characteristic	Symbol	Value	Units
Drain-Source Voltage	V _{DSS}	-50	V
Drain-Gate Voltage (Note 4)	V _{DGR}	-50	V
Gate-Source Voltage	V _{GSS}	±20	V
Drain Current (Note 4)	I _D	-130	mA
Pulsed Drain Current (Note 4)	I _{DM}	-1	A

Thermal Characteristics

Characteristic	Symbol	Value	Units
Total Power Dissipation (Note 4)	P _d	200	mW
Thermal Resistance, Junction to Ambient	R _{θJA}	625	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = 25°C unless otherwise specified)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 5)						
Drain-Source Breakdown Voltage	BV _{DSS}	-50	-75	—	V	V _{GS} = 0V, I _D = -250μA
Zero Gate Voltage Drain Current	I _{DSS}	—	—	-15	μA	V _{DS} = -50V, V _{GS} = 0V, T _J = 25°C
		—	—	-60	μA	V _{DS} = -50V, V _{GS} = 0V, T _J = 125°C
		—	—	-100	nA	V _{DS} = -25V, V _{GS} = 0V, T _J = 25°C
Gate-Body Leakage	I _{GSS}	—	—	±10	nA	V _{GS} = ±20V, V _{DS} = 0V
ON CHARACTERISTICS (Note 5)						
Gate Threshold Voltage	V _{GS(th)}	-0.8	-1.6	-2.0	V	V _{DS} = V _{GS} , I _D = -1mA
Static Drain-Source On-Resistance	R _{DS(ON)}	—	6	10	Ω	V _{GS} = -5V, I _D = -0.100A
Forward Transconductance	g _{FS}	.05	—	—	S	V _{DS} = -25V, I _D = -0.1A
DYNAMIC CHARACTERISTICS						
Input Capacitance	C _{iss}	—	—	45	pF	V _{DS} = -25V, V _{GS} = 0V, f = 1.0MHz
Output Capacitance	C _{oss}	—	—	25	pF	
Reverse Transfer Capacitance	C _{rss}	—	—	12	pF	
SWITCHING CHARACTERISTICS						
Turn-On Delay Time	t _{D(ON)}	—	10	—	ns	V _{DD} = -30V, I _D = -0.27A,
Turn-Off Delay Time	t _{D(OFF)}	—	18	—	ns	R _{GEN} = 50Ω, V _{GS} = -10V

- Notes:
- Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch; pad layout as shown on Diodes Inc. suggested pad layout document AP02001, which can be found on our website at <http://www.diodes.com/datasheets/ap02001.pdf>.
 - Short duration pulse test used to minimize self-heating effect.

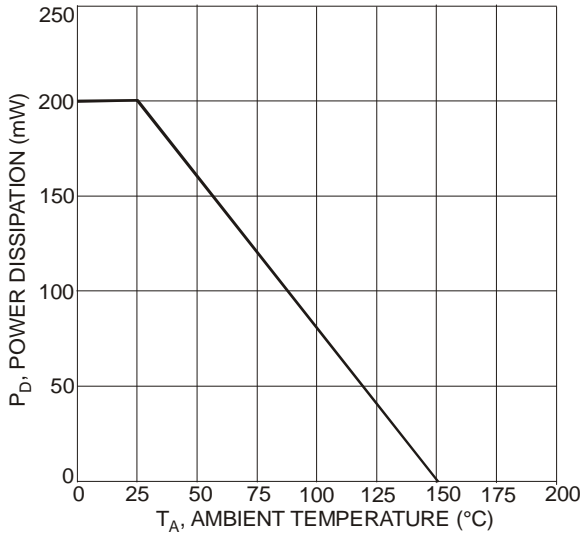


Fig. 1 Max Power Dissipation vs. Ambient Temperature

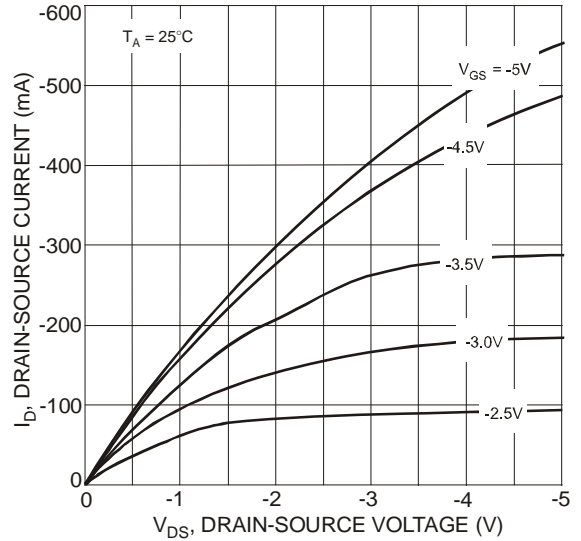


Fig. 2 Drain-Source Current vs. Drain-Source Voltage

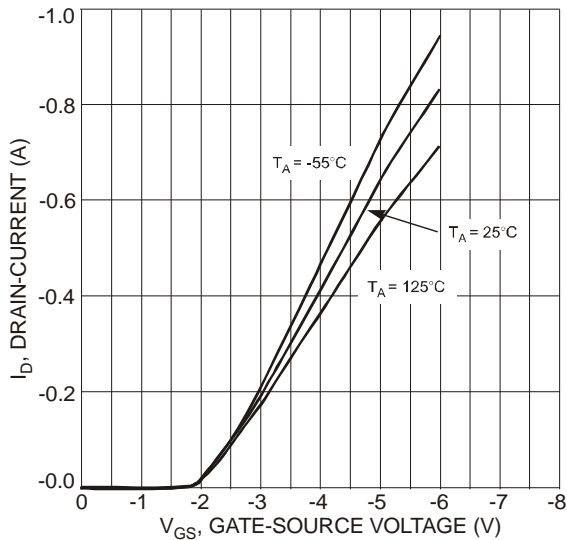


Fig. 3 Drain-Current vs. Gate-Source Voltage

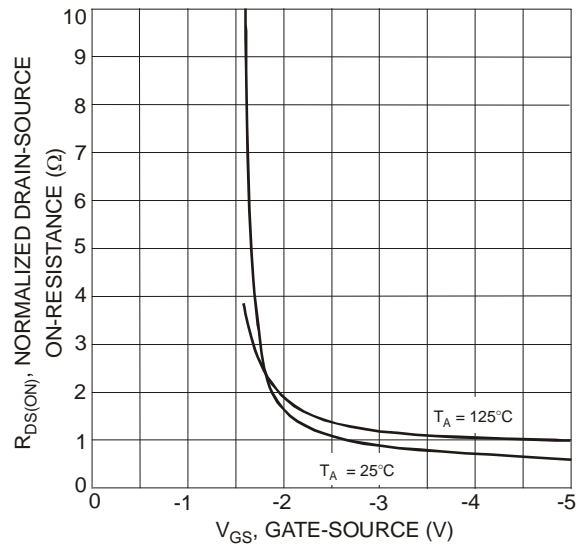


Fig. 4 On-Resistance vs. Gate-Source Voltage

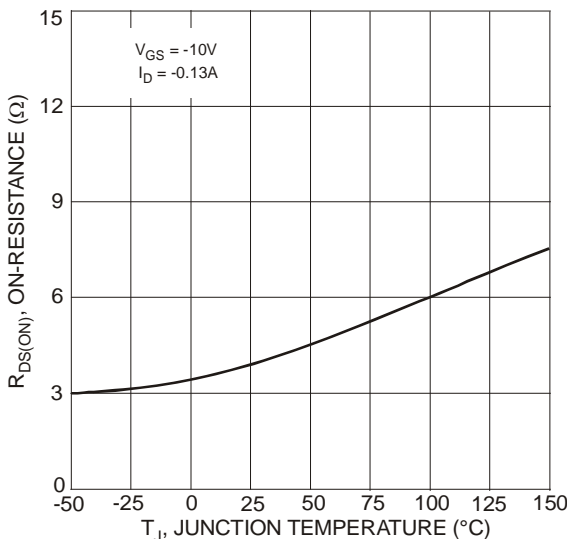


Fig. 5 On-Resistance vs. Junction Temperature

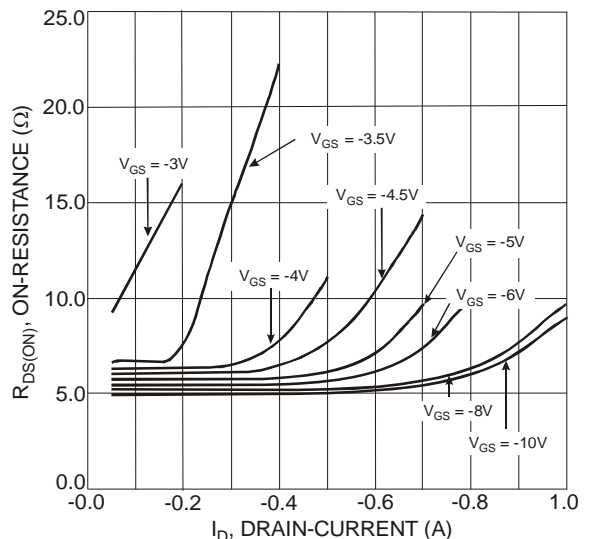
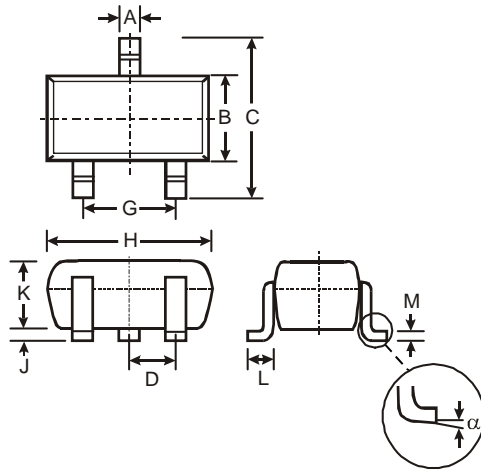


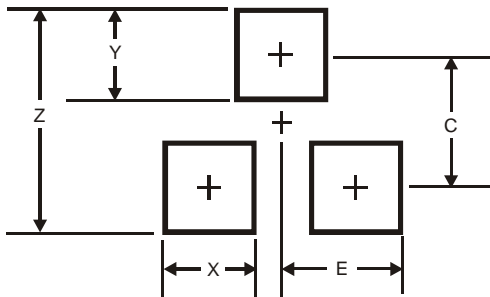
Fig. 6 On-Resistance vs. Drain-Current

Package Outline Dimensions



SOT323			
Dim	Min	Max	Typ
A	0.25	0.40	0.30
B	1.15	1.35	1.30
C	2.00	2.20	2.10
D	-	-	0.65
G	1.20	1.40	1.30
H	1.80	2.20	2.15
J	0.0	0.10	0.05
K	0.90	1.00	1.00
L	0.25	0.40	0.30
M	0.10	0.18	0.11
α	0°	8°	-
All Dimensions in mm			

Suggested Pad Layout



Dimensions	Value (in mm)
Z	2.8
X	0.7
Y	0.9
C	1.9
E	1.0

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